

74AHC2G241-Q100; 74AHCT2G241-Q100

Dual buffer/line driver; 3-state

Rev. 1 — 12 November 2013

Product data sheet

1. General description

The 74AHC2G241-Q100 and 74AHCT2G241-Q100 are high-speed Si-gate CMOS devices. They provide a dual non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $\overline{1OE}$ and 2OE. A HIGH level at pin $\overline{1OE}$ causes output 1Y to assume a high-impedance OFF-state. A LOW level at pin 2OE causes output 2Y to assume a high-impedance OFF-state. Schmitt-trigger action at all inputs makes the circuit highly tolerant for slower input rise and fall times.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC2G241DP-Q100 74AHCT2G241DP-Q100	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHC2G241DC-Q100 74AHCT2G241DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

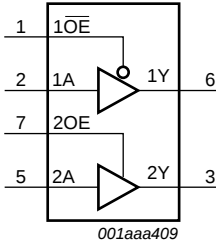
4. Marking

Table 2. Marking

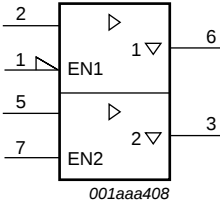
Type number	Marking code ^[1]
74AHC2G241DP-Q100	A241
74AHCT2G241DP-Q100	C241
74AHC2G241DC-Q100	A41
74AHCT2G241DC-Q100	C41

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



The logic symbol shows a rectangular package with pins 1, 2, 7, and 5 on the left, and pins 6, 3, and 4 on the right. Inside, there are two inverters. The first inverter has input 1A (pin 2) and output 1Y (pin 6). The second inverter has input 2A (pin 5) and output 2Y (pin 3). Enable inputs 1OE (pin 1) and 2OE (pin 7) are shown with bubbles. The symbol is labeled 001aaa409.



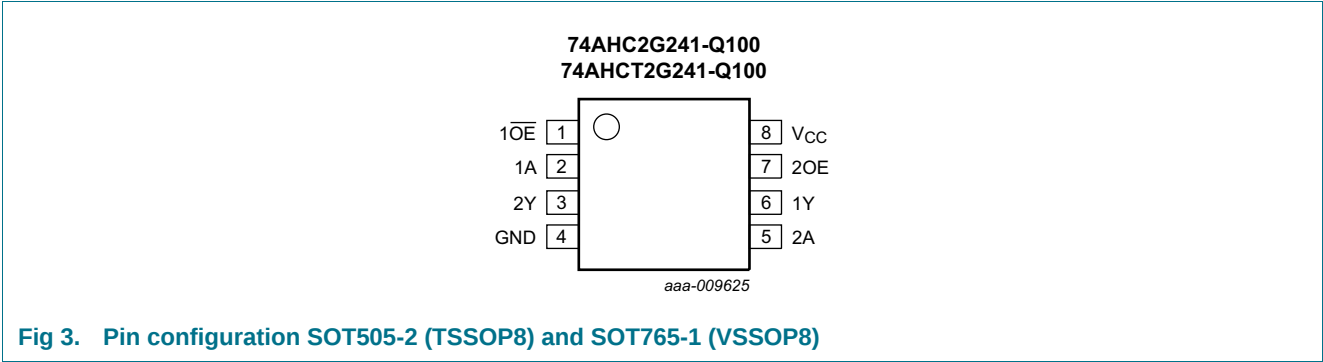
The IEC logic symbol shows a rectangular package with pins 2, 1, 5, and 7 on the left, and pins 6, 3, and 4 on the right. Inside, there are two buffers. The first buffer has input 1A (pin 2) and output 1Y (pin 6). The second buffer has input 2A (pin 5) and output 2Y (pin 3). Enable inputs EN1 (pin 1) and EN2 (pin 7) are shown with triangles. The symbol is labeled 001aaa408.

Fig 1. Logic symbol

Fig 2. IEC logic symbol

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1OE	1	output enable input (active LOW)
1A	2	data input
2Y	3	data output
GND	4	ground (0 V)
2A	5	data input
1Y	6	data output
2OE	7	output enable input (active HIGH)
Vcc	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output	Input		Output
1OE	1A	1Y	2OE	2A	2Y
L	L	L	H	L	L
L	H	H	H	H	H
H	X	Z	L	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[2] -	± 20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V	-	± 25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G241-Q100			74AHCT2G241-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3$ V ± 0.3 V	-	-	100	-	-	-	ns/V
		$V_{CC} = 5.0$ V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G241-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = –50 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –50 µA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = –50 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = –8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	µA
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT2G241-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V

Table 7. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{OZ}	OFF-state output current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	0.25	-	2.5	-	10	μ A
I_I	input leakage current	$V_I = 5.5$ V or GND; $V_{CC} = 0$ V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μ A
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	1.0	-	10	-	40	μ A
ΔI_{CC}	additional supply current	per input pin; $V_I = 3.4$ V; other inputs at V_{CC} or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics
 GND = 0 V; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G241-Q100										
t _{pd}	propagation delay	nA to nY; see Figure 4	[1]							
		V _{CC} = 3.0 V to 3.6 V	[2]							
		C _L = 15 pF	-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF	-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]							
		C _L = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF	-	4.7	7.5	1.0	8.5	1.0	9.5	ns
t _{en}	enable time	1OE to 1Y; see Figure 5	[1]							
		V _{CC} = 3.0 V to 3.6 V	[2]							
		C _L = 15 pF	-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF	-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]							
		C _L = 15 pF	-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		C _L = 50 pF	-	4.9	7.5	1.0	8.5	1.0	9.5	ns
		2OE to 2Y; see Figure 6	[1]							
		V _{CC} = 3.0 V to 3.6 V	[2]							
		C _L = 15 pF	-	4.9	8.0	1.0	9.5	1.0	10.0	ns
		C _L = 50 pF	-	7.0	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]							
		C _L = 15 pF	-	3.6	5.6	1.0	6.3	1.0	7.0	ns
		C _L = 50 pF	-	5.4	8.0	1.0	9.0	1.0	9.5	ns

Table 8. Dynamic characteristics ...continued
GND = 0 V; for test circuit see Figure 7.

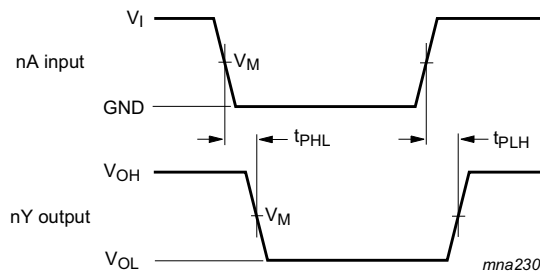
Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{dis}	disable time	$1\overline{OE}$ to 1Y; see Figure 5 [1]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ [2]								
		$C_L = 15\text{ pF}$	-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		$C_L = 50\text{ pF}$	-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ [3]								
		$C_L = 15\text{ pF}$	-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50\text{ pF}$	-	5.7	8.8	1.0	10.0	1.0	11.0	ns
		2OE to 2Y; see Figure 6 [1]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ [2]								
		$C_L = 15\text{ pF}$	-	6.3	9.7	1.0	11.5	1.0	12.5	ns
		$C_L = 50\text{ pF}$	-	9.0	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ [3]								
		$C_L = 15\text{ pF}$	-	4.3	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50\text{ pF}$	-	6.1	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50\text{ pF}$; $f_i = 1\text{ MHz}$; $V_I = \text{GND to }V_{CC}$ [4]	-	10	-	-	-	-	-	pF
74AHCT2G241-Q100										
t_{pd}	propagation delay	nA to nY; see Figure 4 [1]								
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ [3]								
		$C_L = 15\text{ pF}$	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50\text{ pF}$	-	4.7	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	$1\overline{OE}$ to 1Y; see Figure 5 [1]								
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ [3]								
		$C_L = 15\text{ pF}$	-	3.9	5.1	1.0	6.0	1.0	6.5	ns
		$C_L = 50\text{ pF}$	-	5.1	7.5	1.0	8.5	1.0	9.5	ns
		2OE to 2Y; see Figure 6 [1]								
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ [3]								
		$C_L = 15\text{ pF}$	-	3.4	5.6	1.0	6.3	1.0	6.5	ns
		$C_L = 50\text{ pF}$	-	4.8	7.5	1.0	9.0	1.0	9.5	ns

Table 8. Dynamic characteristics ...continued
GND = 0 V; for test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{dis}	disable time	$\overline{1OE}$ to 1Y; see Figure 5 [1]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ [3]								
		$C_L = 15 \text{ pF}$	-	4.5	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50 \text{ pF}$	-	6.1	8.8	1.0	10.0	1.0	11.0	ns
		2OE to 2Y; see Figure 6 [1]								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ [3]								
		$C_L = 15 \text{ pF}$	-	4.0	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50 \text{ pF}$	-	5.7	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$; $f_i = 1 \text{ MHz}$; $V_i = \text{GND to } V_{CC}$	[4]	-	10	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
 t_{en} is the same as t_{PZL} and t_{PZH} .
 t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [2] Typical values are measured at $V_{CC} = 3.3 \text{ V}$.
- [3] Typical values are measured at $V_{CC} = 5.0 \text{ V}$.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V.

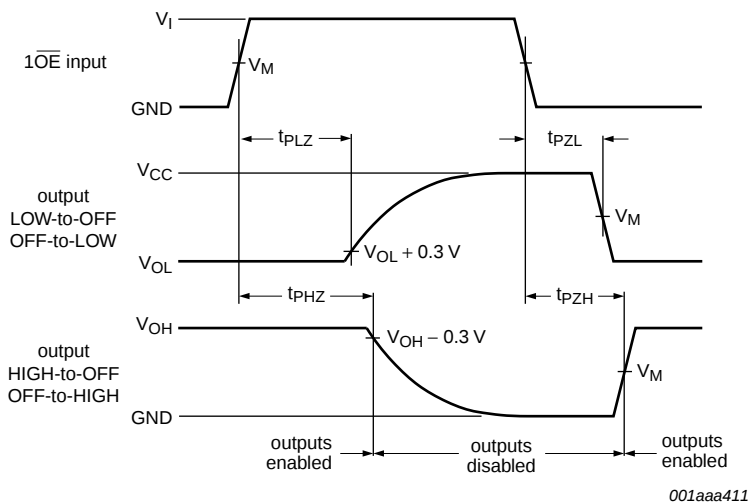
12. Waveforms and test circuit



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

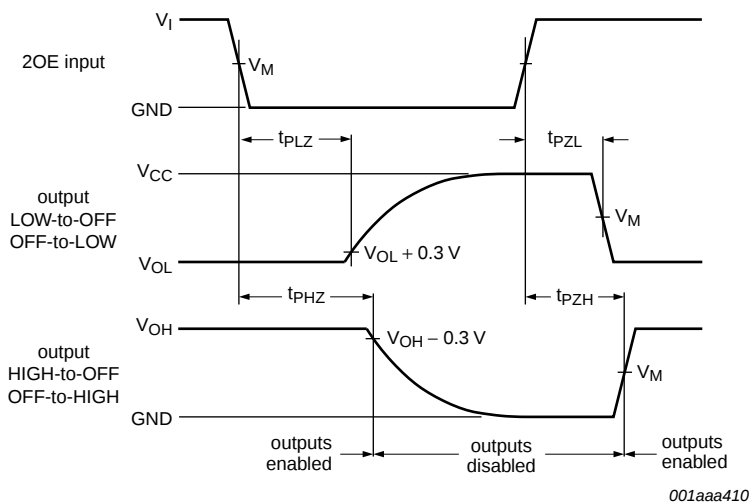
Fig 4. The input (nA) to output (nY) propagation delays



Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The input (1OE) to output (1Y) enable and disable times



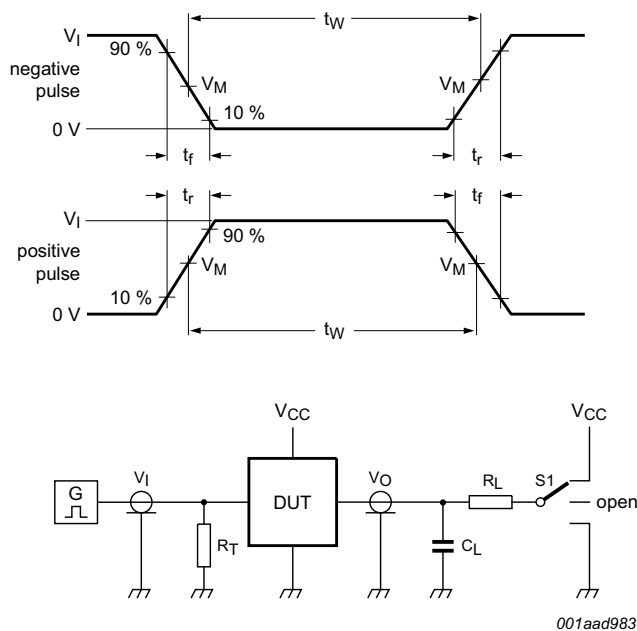
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The input (2OE) to output (2Y) enable and disable times

Table 9. Measurement points

Type	Input	Output
	V_M	V_M
74AHC2G241-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74AHCT2G241-Q100	1.5 V	$0.5V_{CC}$



Test data is given in [Table 10](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC2G241-Q100	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74AHCT2G241-Q100	3 V	≤ 3 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

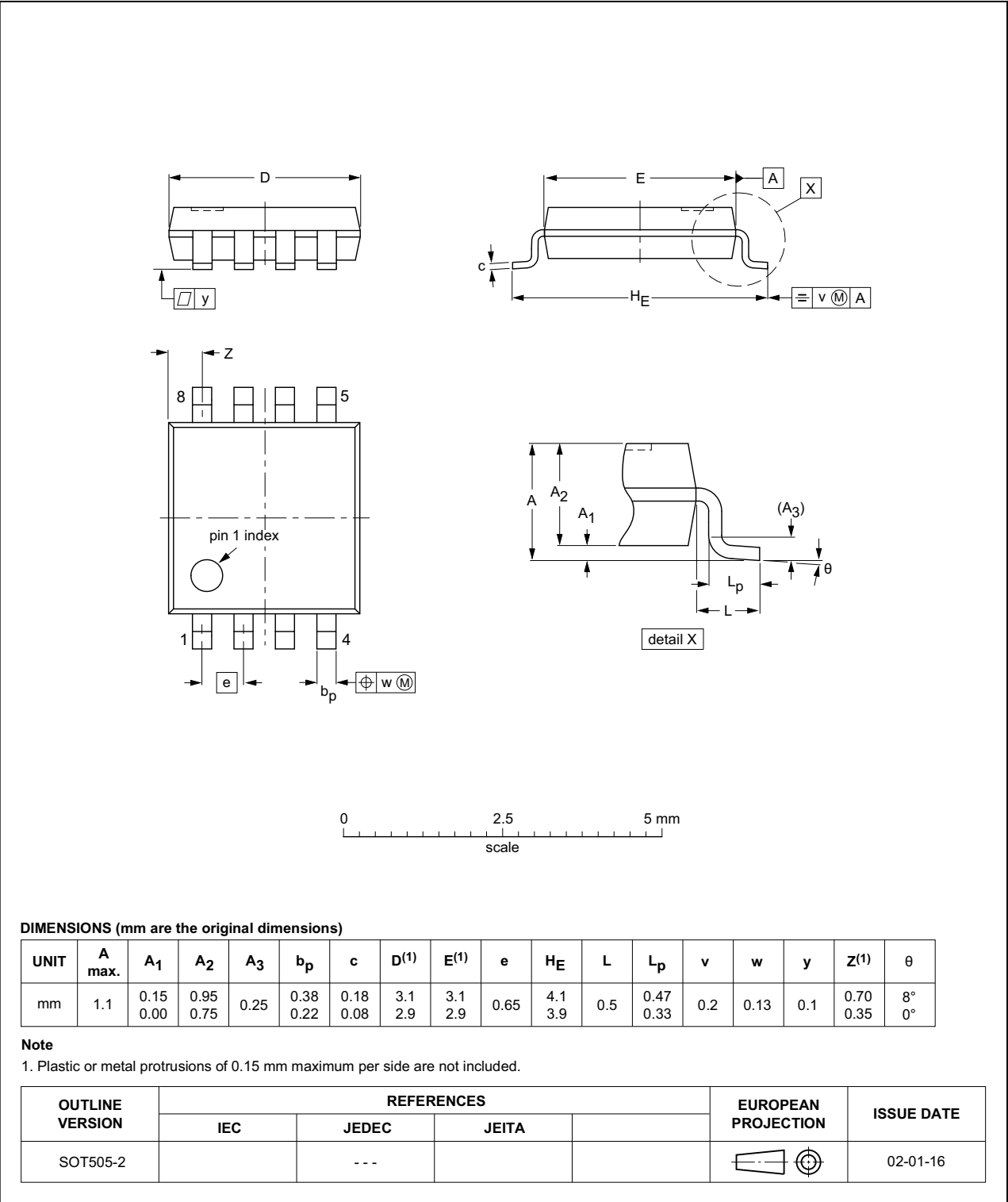


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

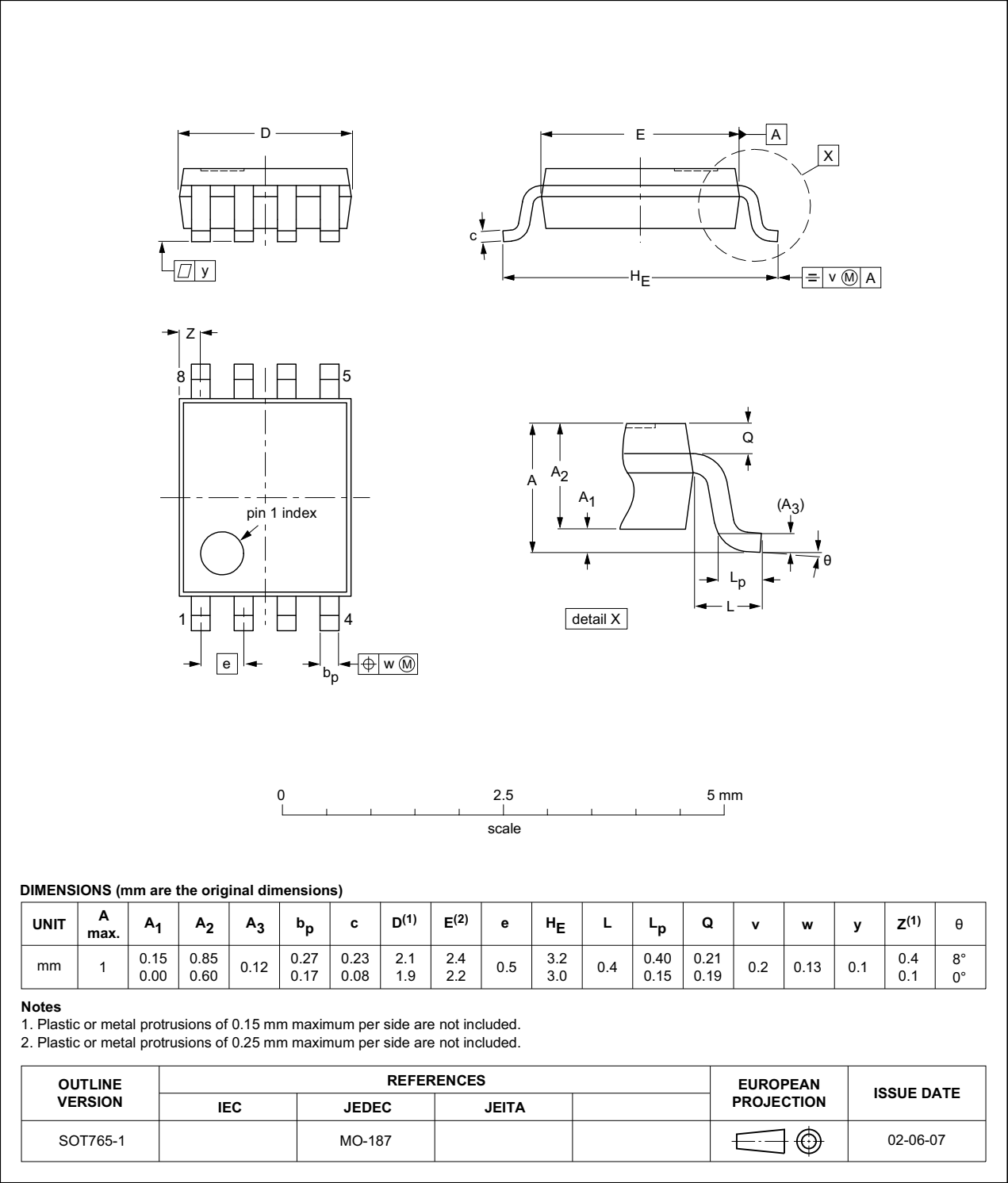


Fig 9. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G241_Q100 v.1	20131112	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

18. Contents

1	General description	1
2	Features and benefits	1
3	Ordering information	2
4	Marking	2
5	Functional diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	3
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	5
11	Dynamic characteristics	6
12	Waveforms and test circuit	8
13	Package outline	11
14	Abbreviations	13
15	Revision history	13
16	Legal information	14
16.1	Data sheet status	14
16.2	Definitions	14
16.3	Disclaimers	14
16.4	Trademarks	15
17	Contact information	15
18	Contents	16

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2013.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 12 November 2013

Document identifier: 74AHC_AHCT2G241_Q100